

## N-channel Enhancement Mode Power MOSFET

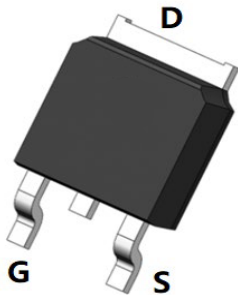
### Features

- $V_{DS} = 60V$ ,  $I_D = 50A$
- $R_{DS(ON)} < 73m\Omega$  @  $V_{GS} = 10V$
- $R_{DS(ON)} < 85 m\Omega$  @  $V_{GS} = 4.5V$

### General Features

- Advanced Trench Technology
- Provide Excellent  $R_{DS(ON)}$  and Low Gate Charge
- Lead Free and Green Available

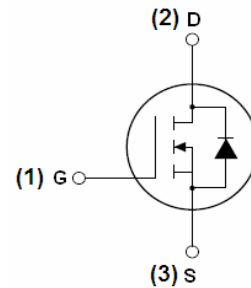
100% UIS TESTED!  
100%  $\Delta V_{ds}$  TESTED!



TO-252-2L Top View



Pin Assignment



Schematic Diagram

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	60	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current	$T_C = 25\text{ }^\circ\text{C}$	$I_D$	18	A
	$T_C = 70\text{ }^\circ\text{C}$		14	
Pulsed Drain Current ( $t = 300\text{ }\mu\text{s}$ )		$I_{DM}$	25	
Avalanche Current		$I_{AS}$	15	
Single Avalanche Energy <sup>a</sup>	$L = 0.1\text{ mH}$	$E_{AS}$	11.25	mJ
Maximum Power Dissipation <sup>a</sup>	$T_C = 25\text{ }^\circ\text{C}$	$P_D$	41.7 <sup>b</sup>	W
	$T_A = 25\text{ }^\circ\text{C}$		2.1	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	- 55 to 150	$^\circ\text{C}$
<b>THERMAL RESISTANCE RATINGS</b>				
Parameter		Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount) <sup>c</sup>		$R_{thJA}$	60	$^\circ\text{C/W}$
Junction-to-Case (Drain)		$R_{thJC}$	3	

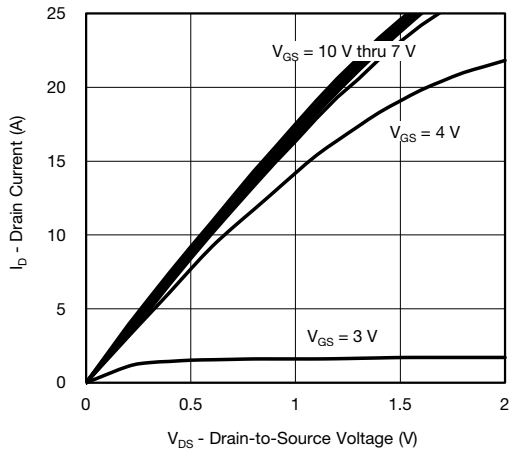
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0		3.0	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 250$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$			250	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 10\text{ V}, V_{GS} = 10\text{ V}$	20			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 6.6\text{ A}$		0.073		$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 6\text{ A}$		0.085		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 6.6\text{ A}$		25		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		660		$\mu\text{F}$
Output Capacitance	$C_{oss}$			85		
Reverse Transfer Capacitance	$C_{rss}$			40		
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 6.6\text{ A}$		19.8	30	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			3.6		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			4.1		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	0.4	2	4	$\Omega$
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 9.6\text{ }\Omega$ $I_D \cong 5.2\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		8	16	ns
Rise Time <sup>c</sup>	$t_r$			11	20	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			18	27	
Fall Time <sup>c</sup>	$t_f$			5	10	
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 9.6\text{ }\Omega$ $I_D \cong 5.2\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		38	57	
Rise Time <sup>c</sup>	$t_r$			58	87	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			18	27	
Fall Time <sup>c</sup>	$t_f$			8	16	
<b>Drain-Source Body Diode Ratings and Characteristics<sup>b</sup></b> $T_C = 25\text{ }^\circ\text{C}$						
Continuous Current	$I_S$				18	A
Pulsed Current	$I_{SM}$				25	
Forward Voltage <sup>a</sup>	$V_{SD}$	$I_F = 5.2\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.5	V
Reverse Recovery Time	$t_{rr}$	$I_F = 5.2\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		34	51	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			3	5	A
Reverse Recovery Charge	$Q_{rr}$				50	75

**Notes:**

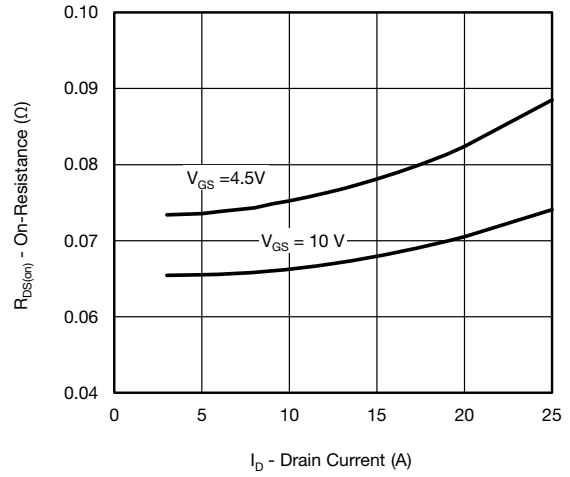
- Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

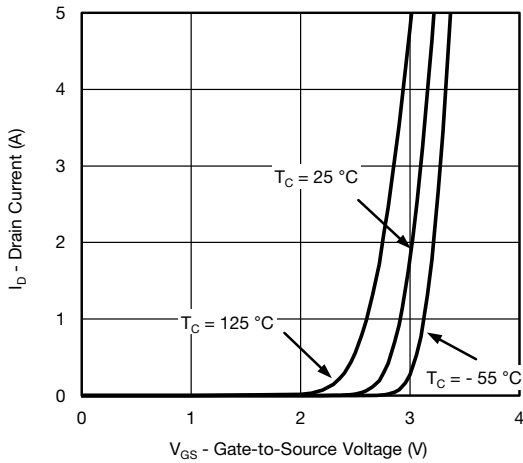
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



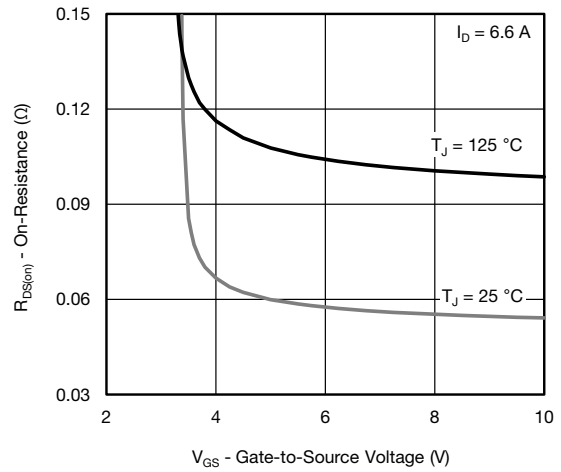
**Output Characteristics**



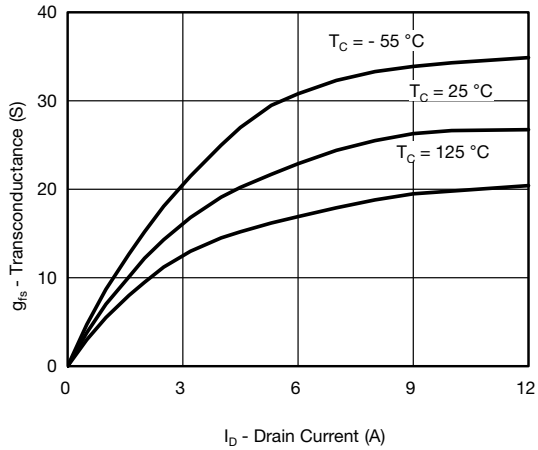
**On-Resistance vs. Drain Current**



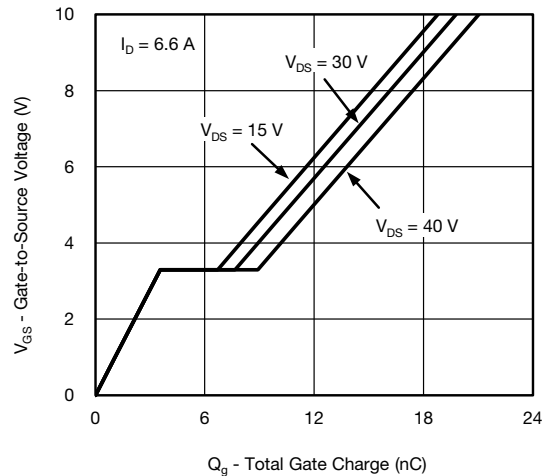
**Transfer Characteristics**



**On-Resistance vs. Gate-to-Source Voltage**

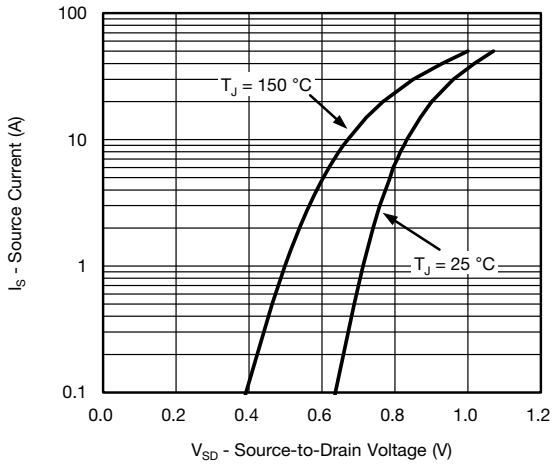


**Transconductance**

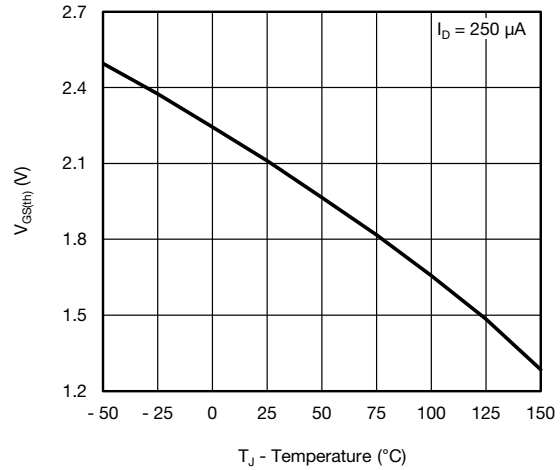


**Gate Charge**

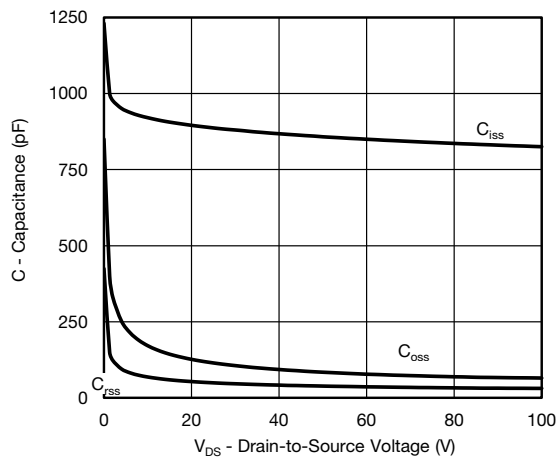
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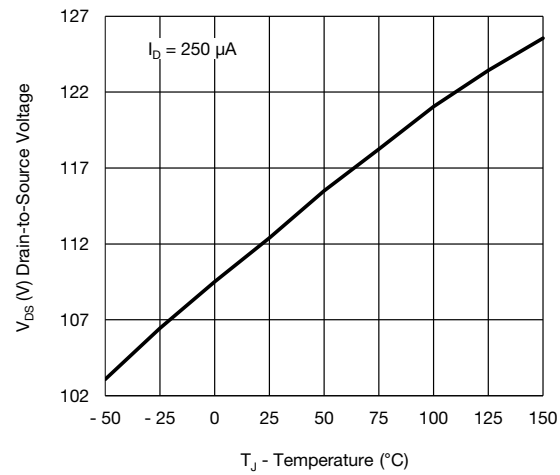
**Source-Drain Diode Forward Voltage**



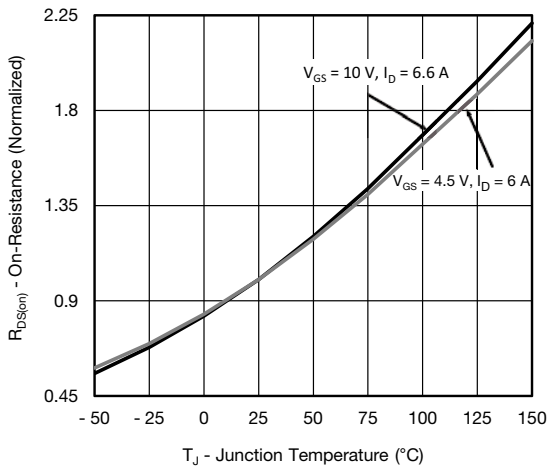
**Threshold Voltage**



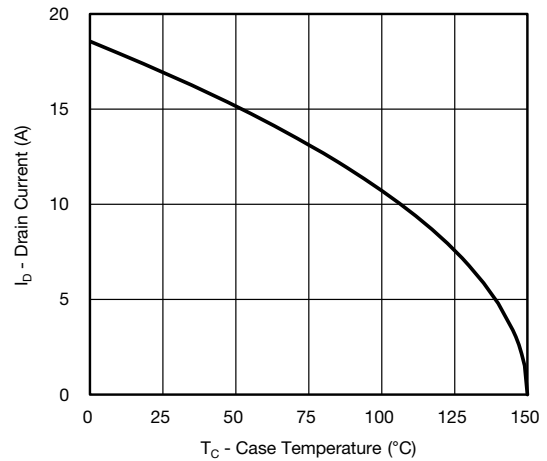
**Capacitance**



**Drain Source Breakdown vs. Junction Temperature**

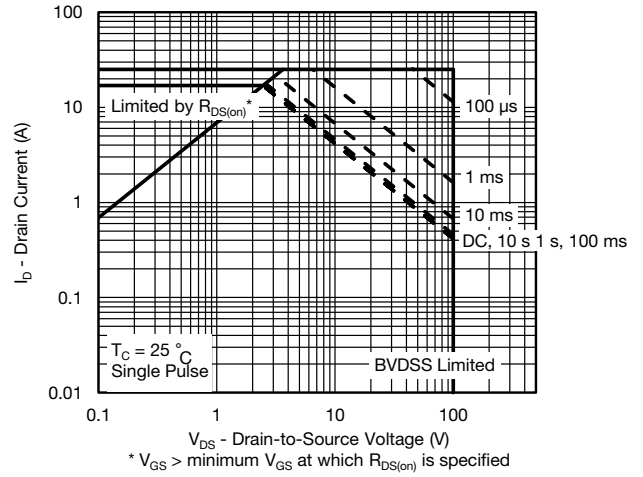
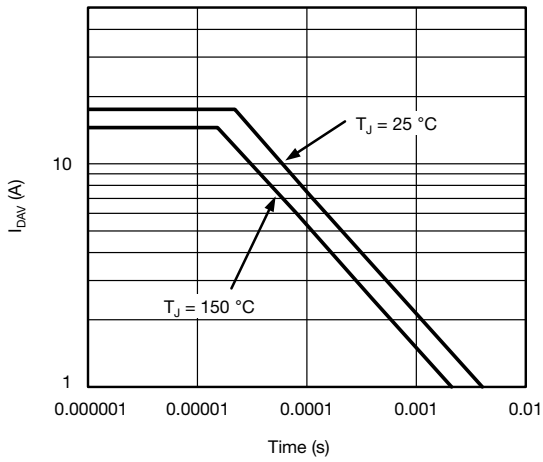


**On-Resistance vs. Junction Temperature**



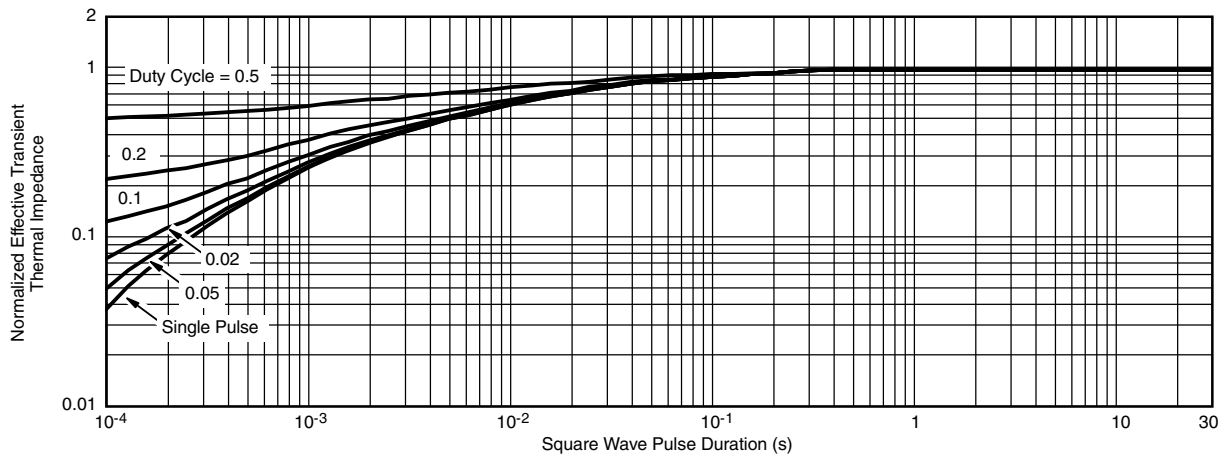
**Current Derating**

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



Single Pulse Avalanche Current Capability vs. Time

Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case